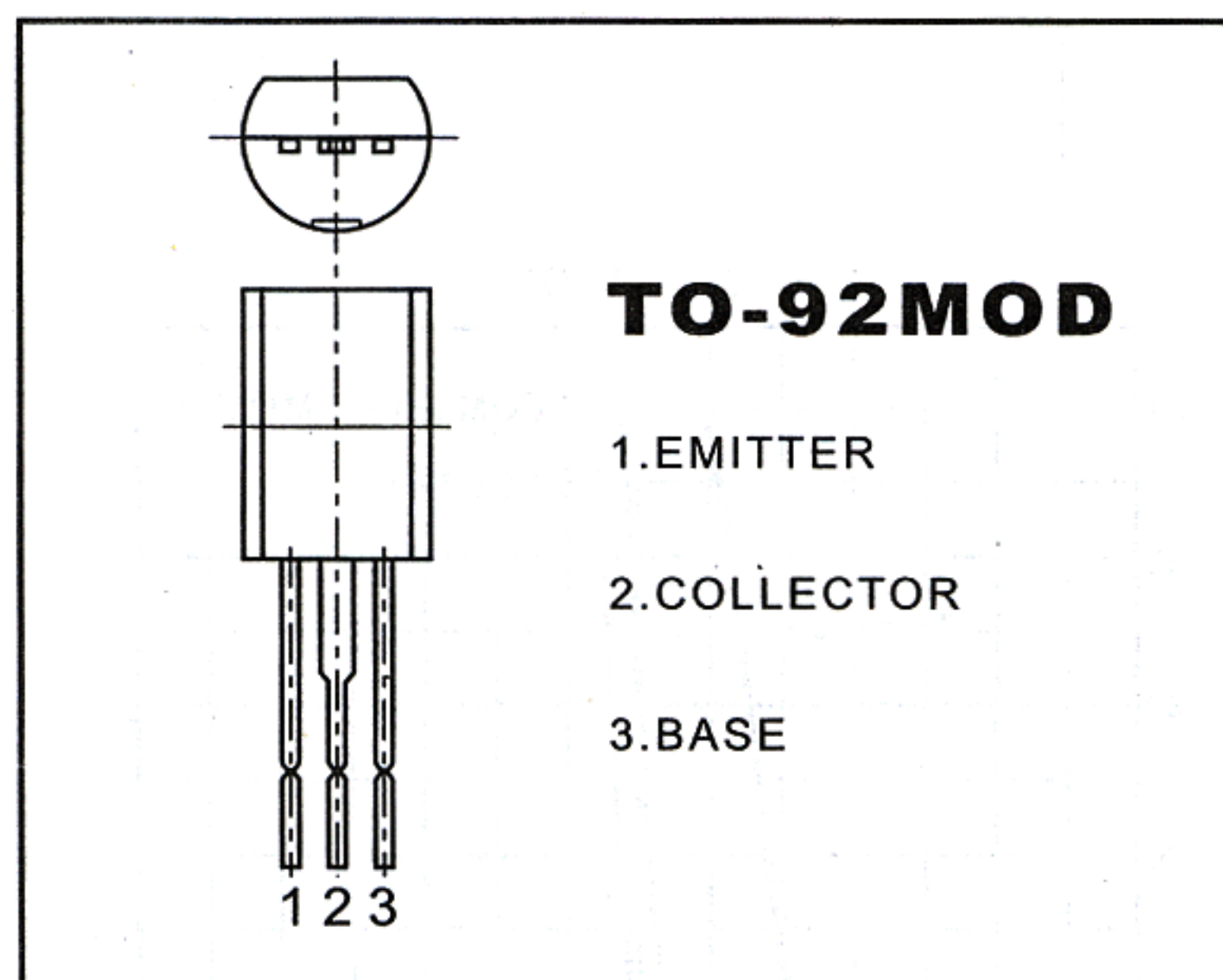


2SC2229 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.8W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 200 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

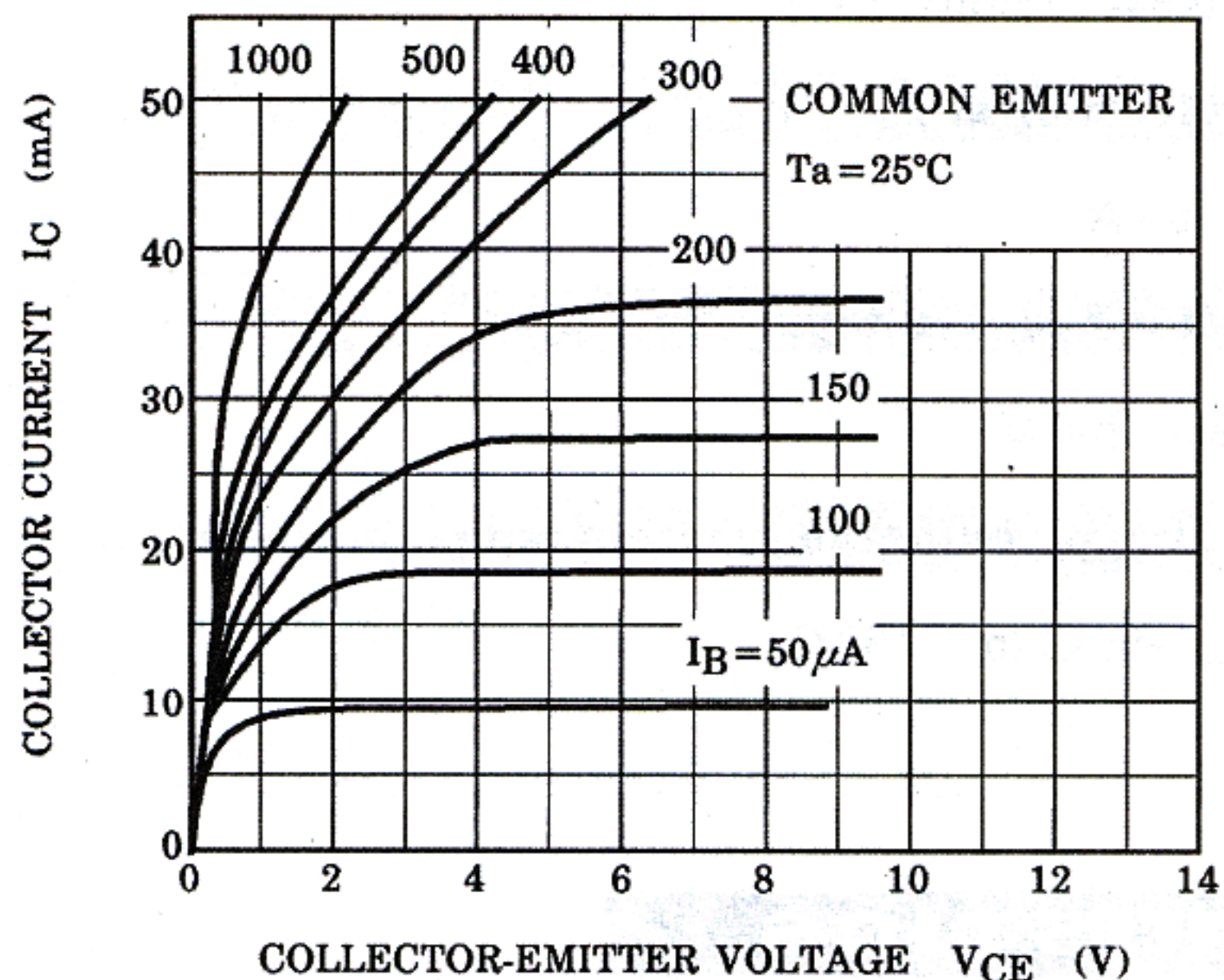
($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	200		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 200 V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CER}	$V_{CB} = 150 V, R_{EB} = 10 M\Omega$		1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 5 V, I_C = 10 mA$	70	240	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 10 mA, I_B = 1 mA$		0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 10 mA, I_B = 1 mA$		1	V
Transition frequency	f_T	$V_{CE} = 30 V, I_C = 10 mA$ $f = 30 MHz$	80		MHz

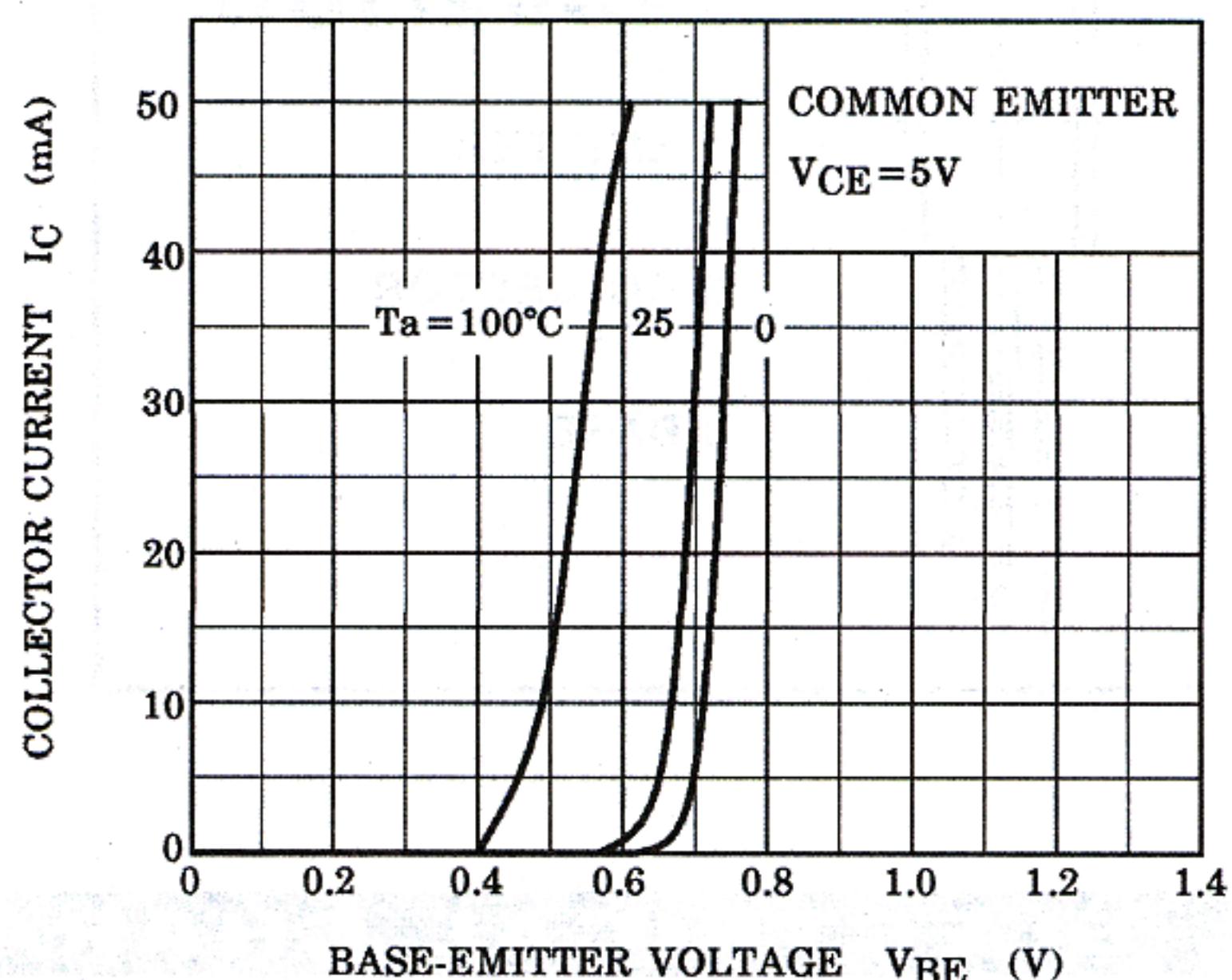
CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240

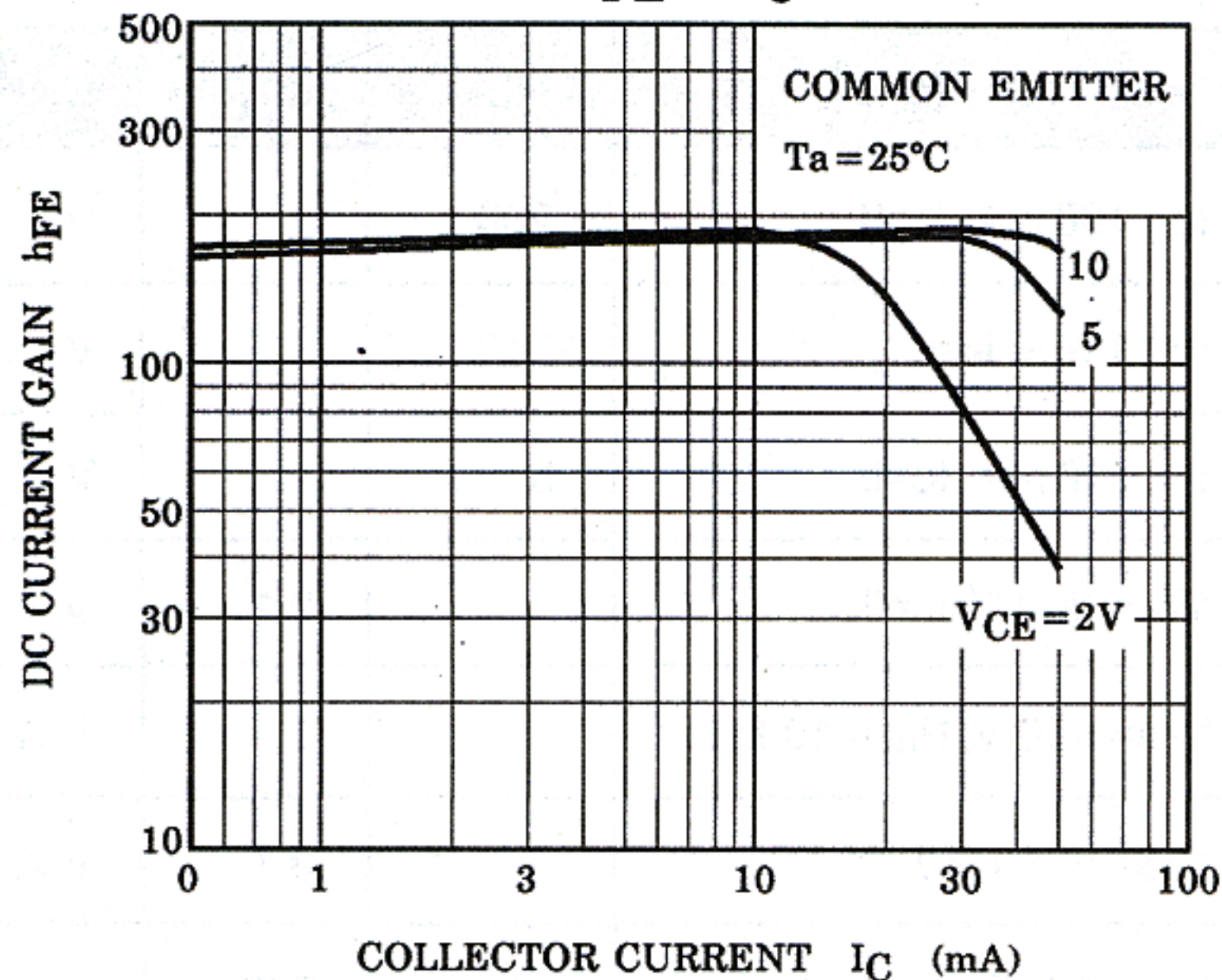
$I_C - V_{CE}$



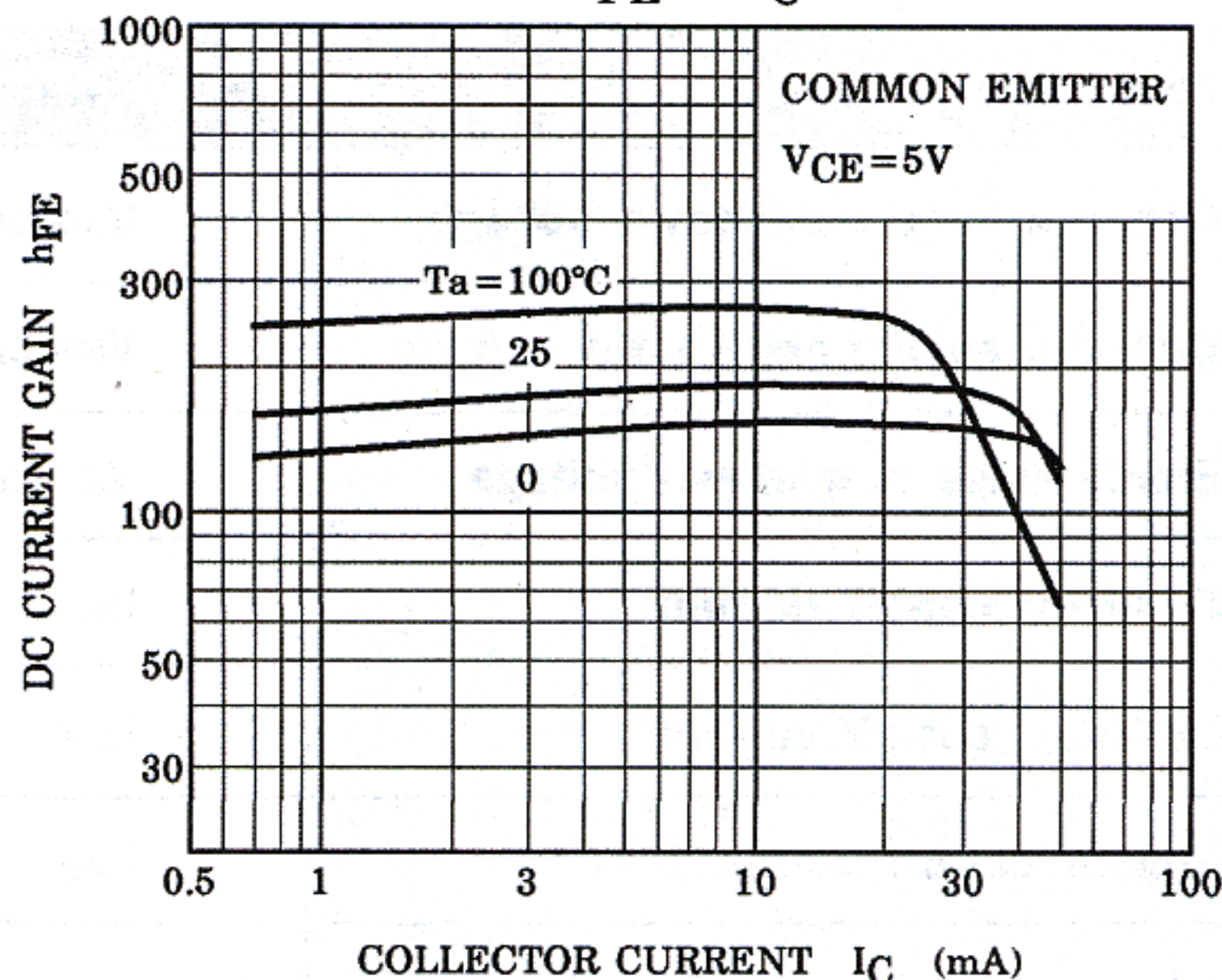
$I_C - V_{BE}$



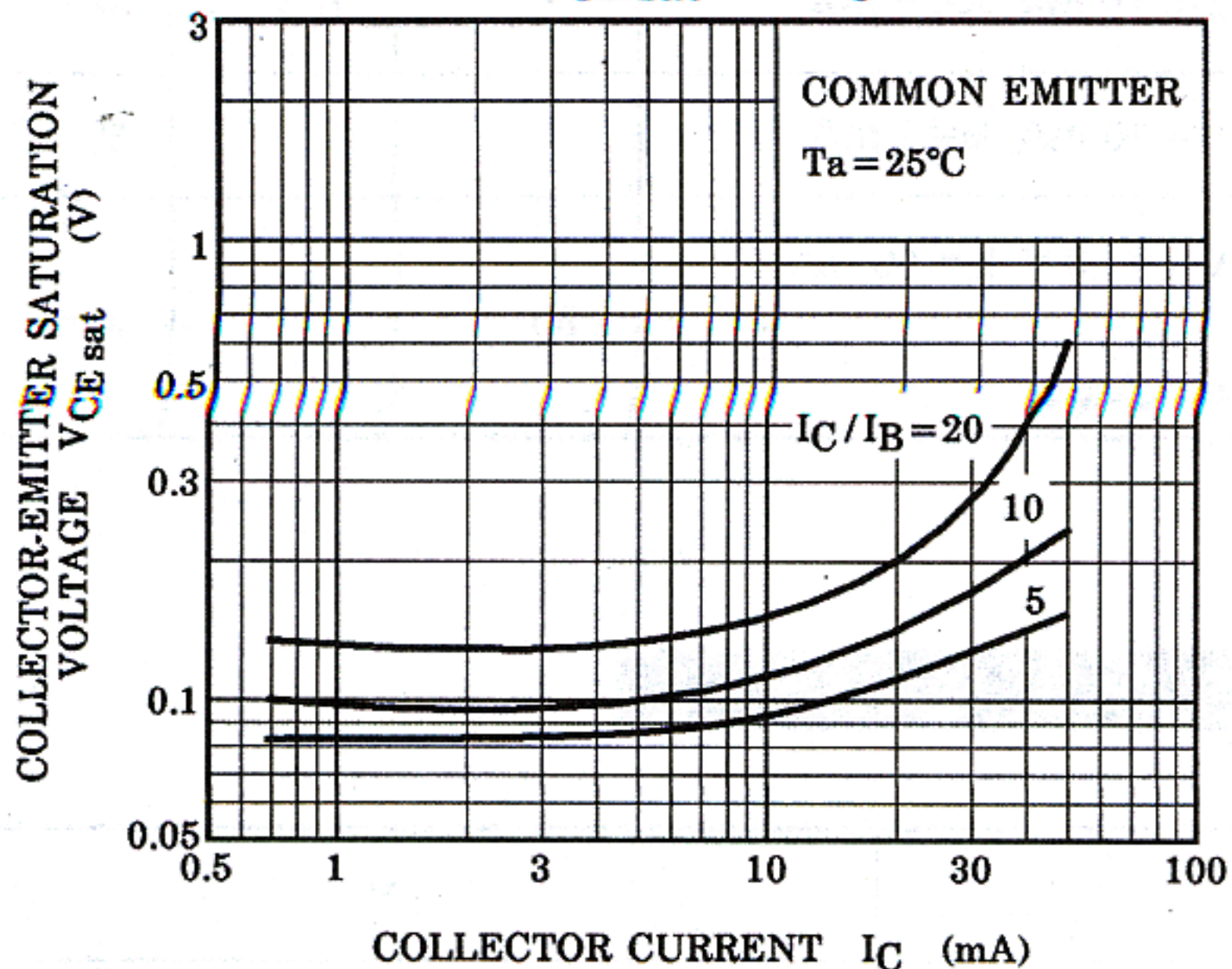
$h_{FE} - I_C$



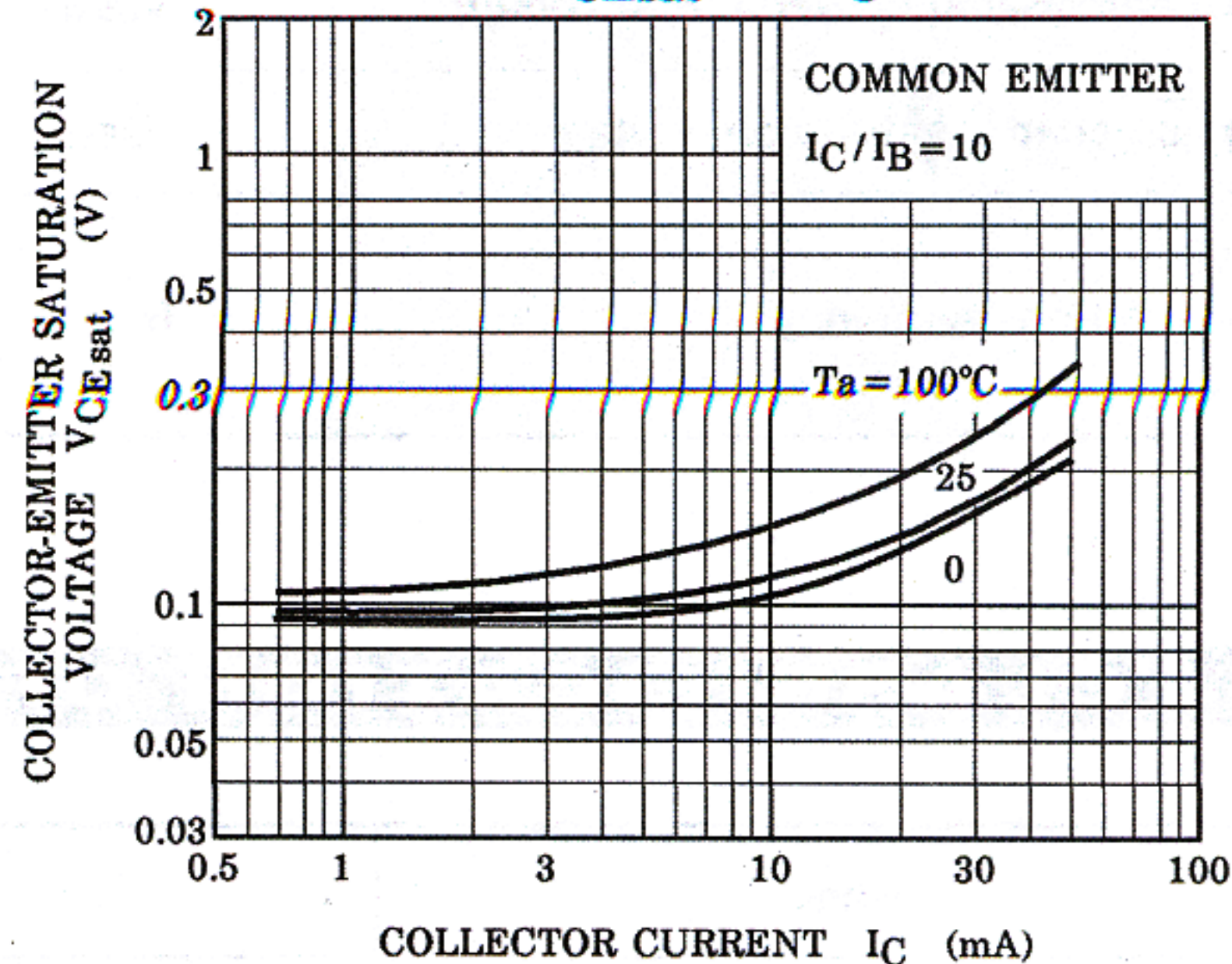
$h_{FE} - I_C$



$V_{CEsat} - I_C$



$V_{CEsat} - I_C$



Typical Characteristics

2SC2229

